					Docket Number (Optional) 15436.170.1		Application Number 10/695,057					
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.												

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Patent and Trademark Office \* U.S. DEPARTMENT OF COMMERCE

			Docket Number (Optional) 15436.170.1	Application Number 10/695,057				
INF	ORMA	ATION DISCLOSURE CITATION	Applicant(s)					
		(Use several sheets if necessary)	Deng et al.  Filing Date  Group Art Unit					
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